

PNP Darlington Transistor

This device is designed for applications requiring extremely high current gain at currents to 800 mA. Sourced from Process 61.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CES}	Collector-Emitter Voltage	30	V	
V _{CBO}	Collector-Base Voltage	30	V	
V _{EBO}	Emitter-Base Voltage	10	V	
Ic	Collector Current - Continuous	1.2	A	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These resteady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах		Units	
		MPSA64	*MMBTA64	**PZTA64	
P _D	Total Device Dissipation	625	350	1,000	mW
	Derate above 25°C	5.0	2.8	8.0	mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	83.3			°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	200	357	125	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

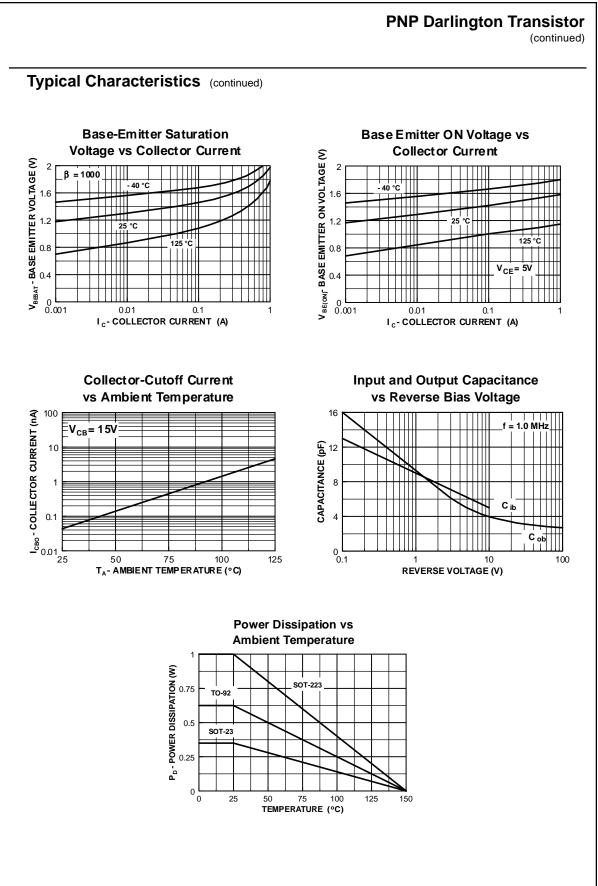
** Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

PNP Darlington Transistor

(continued))
-------------	---

Symbol	Parameter	Test Conditions	Min	Max	Unit
) FF CHAF	RACTERISTICS				
(BR)CES	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm B} = 0$	30		V
BO	Collector-Cutoff Current	$V_{CB} = 30 \text{ V}, I_E = 0$		100	nA
BO	Emitter-Cutoff Current	$V_{EB} = 10 \text{ V}, I_{C} = 0$		100	nA
N CHAR	ACTERISTICS*				
Ē	DC Current Gain	$I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_{C} = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$	10,000 20,000		
CE(sat)	Collector-Emitter Saturation Voltage	$I_{\rm C}$ = 100 mA, $I_{\rm B}$ = 0.1 mA		1.5	V
BE(on)	Base-Emitter On Voltage	I_{C} = 100 mA, V_{CE} = 5.0 V		2.0	V
	GNAL CHARACTERISTICS	$l_{c} = 10 \text{ mA} \text{ V}_{cr} = 5.0 \text{ V}$	125		MHz
*Pulse Test: Pu NOTE: All volta	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Ilse Width ≤ 300 µs, Duty Cycle ≤ 2.0% ges (V) and currents (A) are negative polarity for PNP t	I_{C} = 10 mA, V_{CE} = 5.0 V, f = 100 MHz ransistors.	125		MH2
*Pulse Test: Pu NOTE: All volta	Current Gain - Bandwidth Product Ilse Width ≤ 300 µs, Duty Cycle ≤ 2.0% ges (V) and currents (A) are negative polarity for PNP t I Characteristics	f = 100 MHz		aturation	
*Pulse Test: Pu NOTE: All volta	Current Gain - Bandwidth Product llse Width \leq 300 µs, Duty Cycle \leq 2.0% ges (V) and currents (A) are negative polarity for PNP t	f = 100 MHz ransistors. Collector	-Emitter Sa		

MPSA64 / MMBTA64 / PZTA64



MPSA64 / MMBTA64 / PZTA64



©2001 Fairchild Semiconductor Corporation

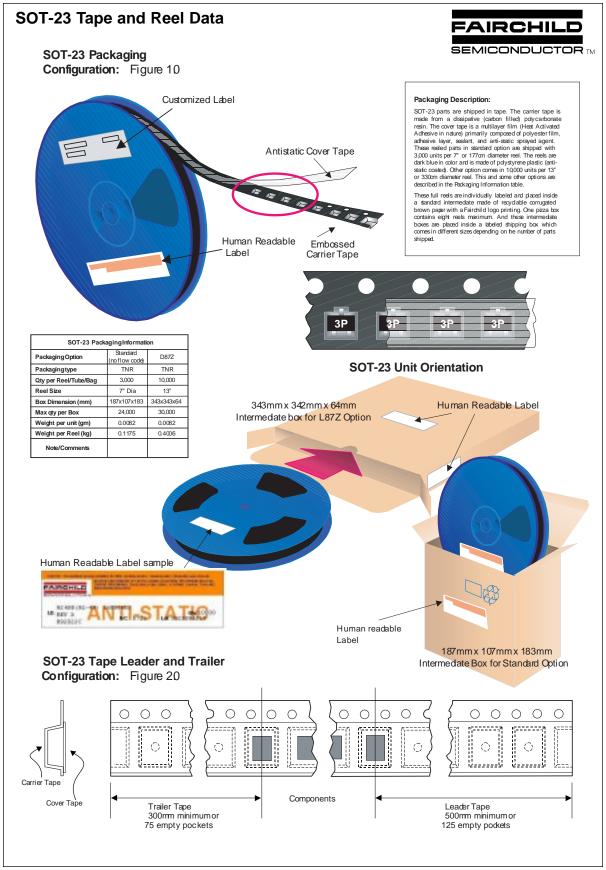
March 2001, Rev. B1





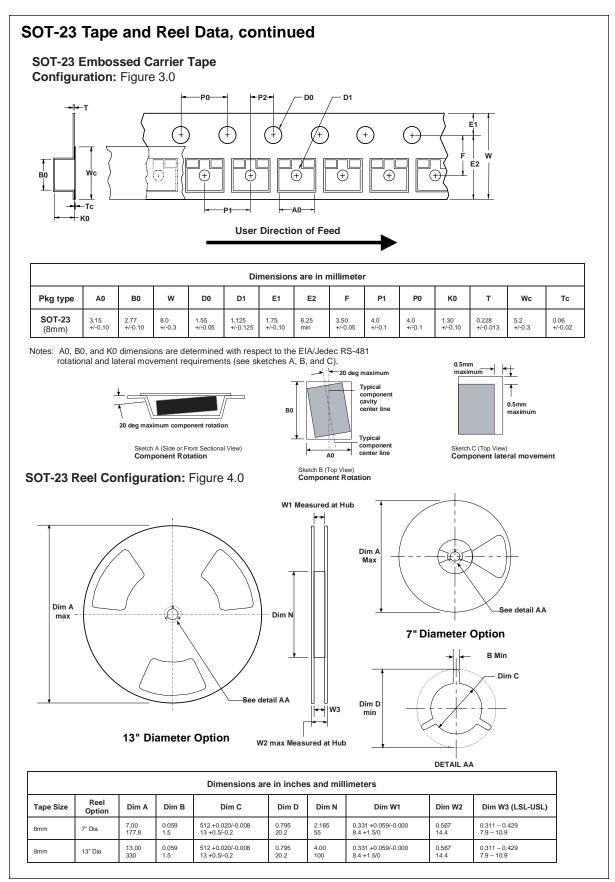
July 1999, Rev. A



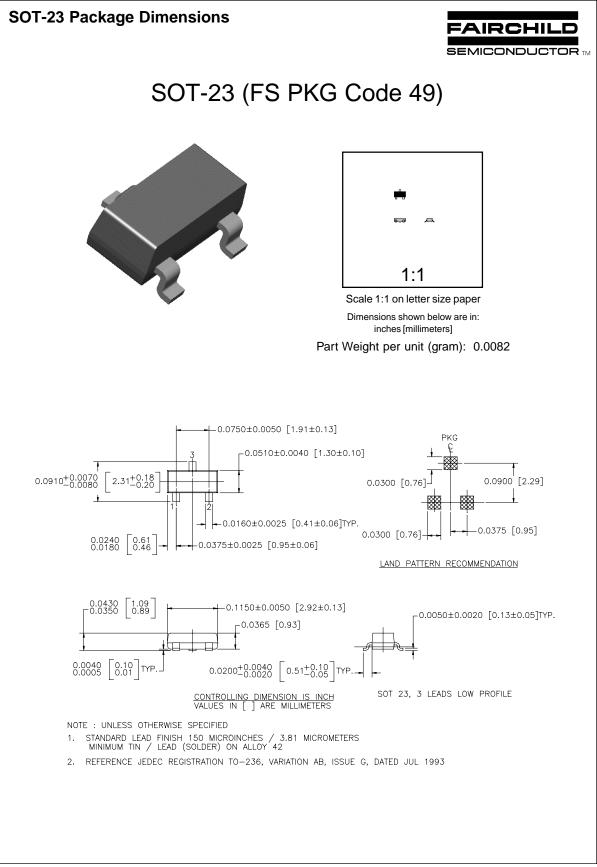


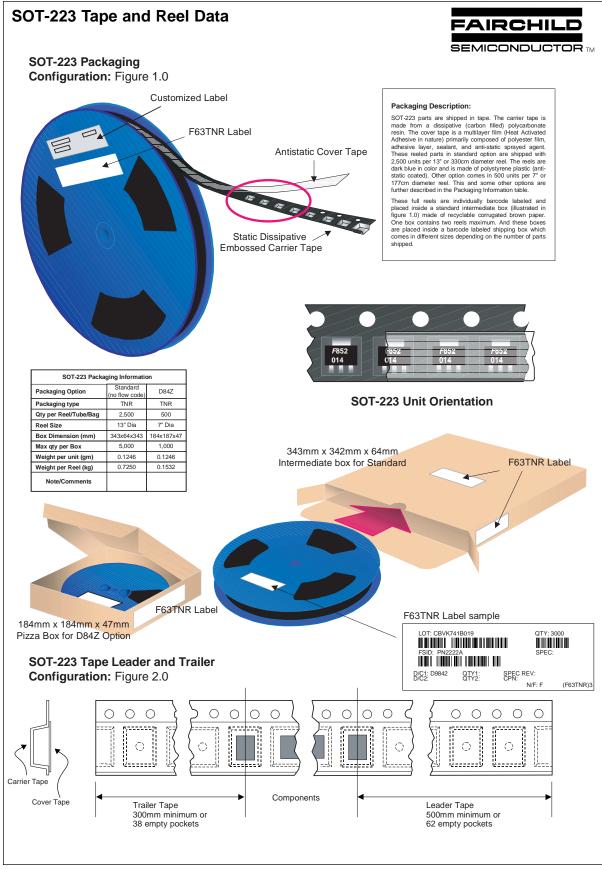
©2000 Fairchild Semiconductor International

September 1999, Rev. C



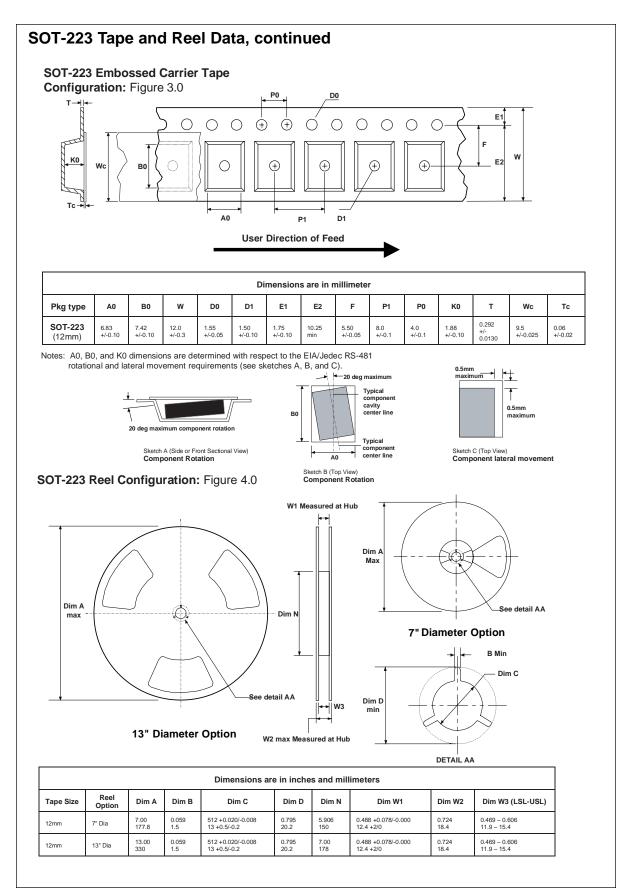
September 1999, Rev. C

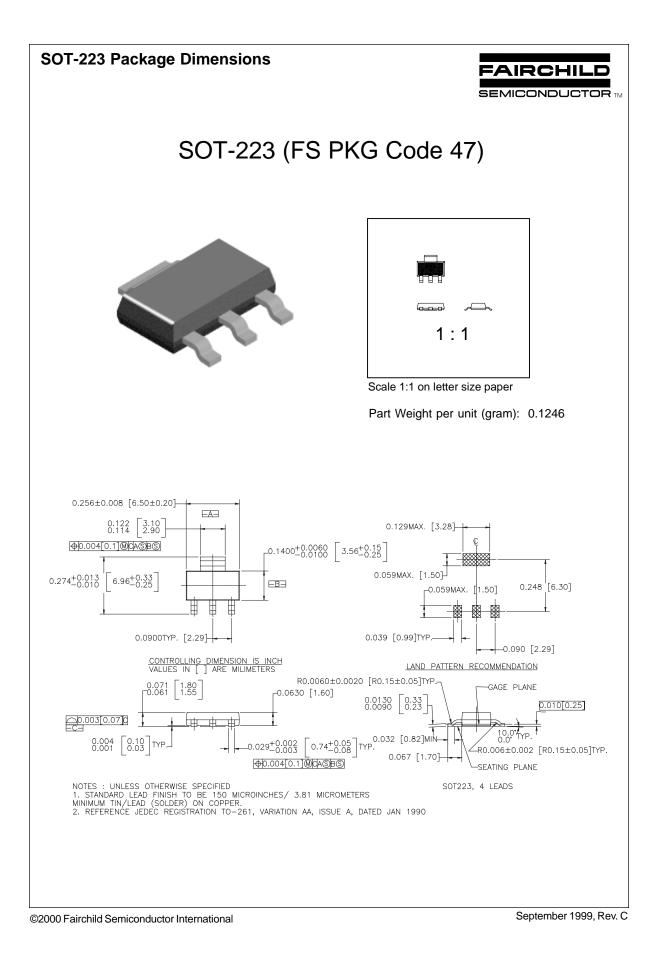




©2000 Fairchild Semiconductor International

September 1999, Rev. B





TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™ Bottomless™ CoolFET™ CROSSVOLT™ DOME™ E²CMOS[™] EnSigna™ FACT™ FACT Quiet Series[™] FAST[®]

FASTr™ GlobalOptoisolator™ GTO™ HiSeC™ **ISOPLANAR™** MICROWIRE™ OPTOLOGIC™ **OPTOPLANAR™** PACMAN™ POP™

PowerTrench[®] QFET™ QS™ QT Optoelectronics[™] Quiet Series[™] SILENT SWITCHER® SMART START™ SuperSOT[™]-3 SuperSOT[™]-6 SuperSOT[™]-8

SyncFET™ TinyLogic™ UHC™ VCX™

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.
	1	Rev G